# Power MOSFET –30V, 73mΩ, –4.5A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

#### Features

- Low On-Resistance
- 1.8V drive
- High Speed Switching
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

#### **Typical Applications**

• DC/DC Converter

#### **SPECIFICATIONS**

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	VGSS	±10	٧
Drain Current (DC)	ID	-4.5	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	-18	Α
Power Dissipation When mounted on ceramic substrate (1500mm² × 0.8mm)	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit		
Junction to Ambient					
When mounted on ceramic substrate	$R_{\theta JA}$	83.3	°C/W		
(1500mm <sup>2</sup> × 0.8mm)					

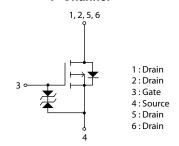


#### ON Semiconductor®

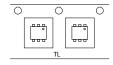
www.onsemi.com

VDSS	R <sub>DS</sub> (on) Max	ID Max
	73mΩ@ –4.5V	
-30V	99mΩ@ −2.5V	-4.5A
	155mΩ@ –1.8V	

## ELECTRICAL CONNECTION P-Channel



#### PACKING TYPE: TL MARKING





#### **ORDERING INFORMATION**

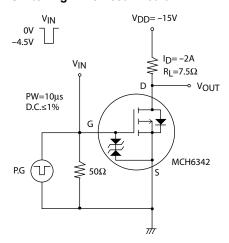
See detailed ordering and shipping information on page 5 of this data sheet.

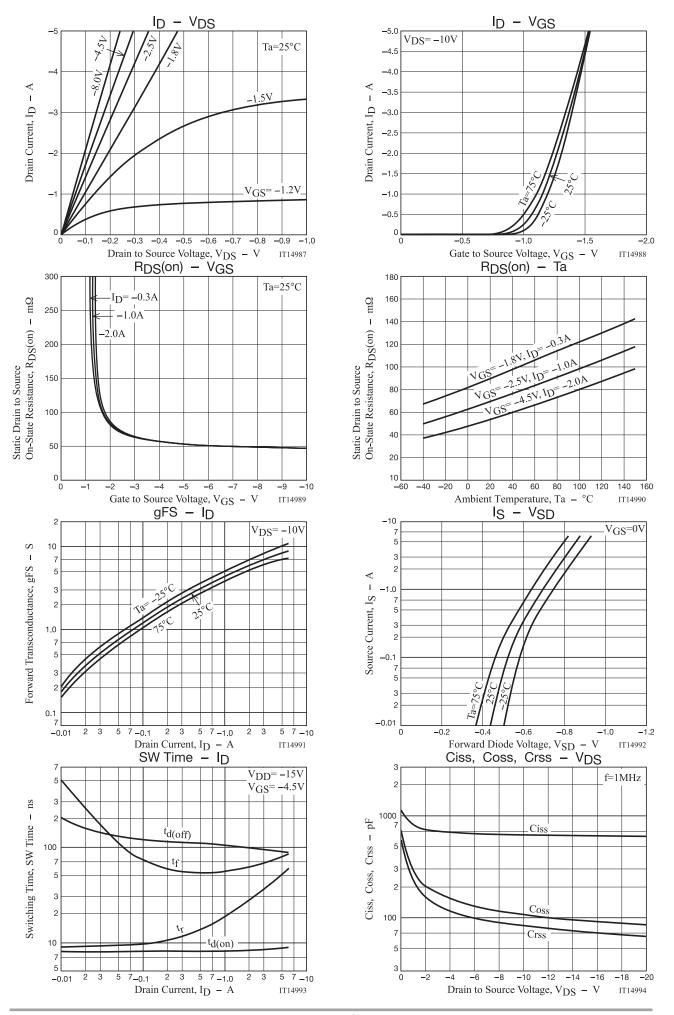
#### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 2)

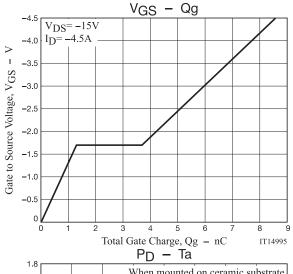
Parameter	Symbol	Conditions	Value			Unit
Farameter	Syllibol	Conditions	min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>G</sub> S=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.4		-1.3	V
Forward Transconductance	gFS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A	3.4	5.8		S
	R <sub>DS</sub> (on)1	I <sub>D</sub> =-2A, V <sub>G</sub> S=-4.5V		56	73	mΩ
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =-1A, V <sub>G</sub> S=-2.5V		71	99	mΩ
Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.3A, V <sub>G</sub> S=-1.8V		95	155	mΩ
Input Capacitance	Ciss			650		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		105		pF
Reverse Transfer Capacitance	Crss			83		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			8.2		ns
Rise Time	tr	On a supplied Took Observit		28		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		100		ns
Fall Time	tf			60		ns
Total Gate Charge	Qg			8.6		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.5A		1.3		nC
Gate to Drain "Miller" Charge	Qgd			2.4		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =-4.5A, V <sub>GS</sub> =0V		-0.83	-1.2	V

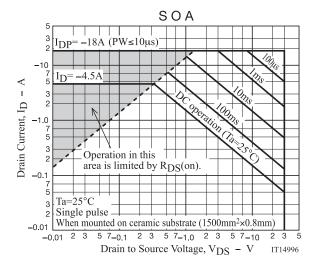
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

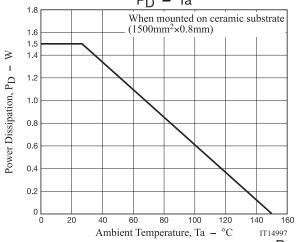
#### **Switching Time Test Circuit**

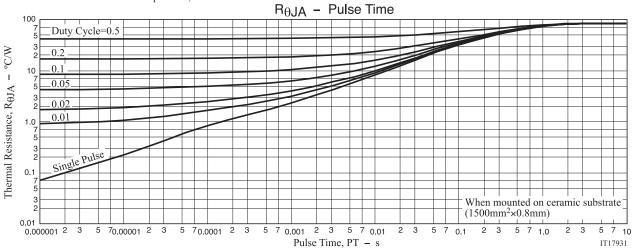








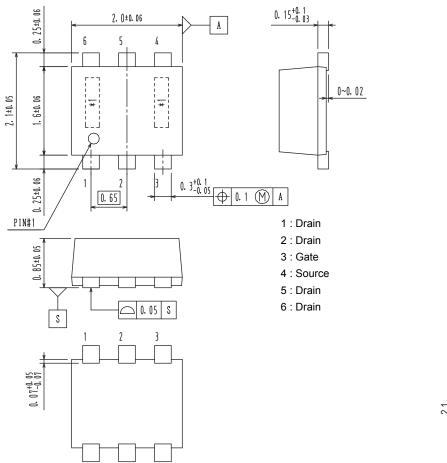




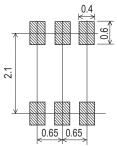
#### PACKAGE DIMENSIONS

unit : mm

SC-88FL / MCPH6 CASE 419AS ISSUE O



#### Recommended Soldering Footprint



#### ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
MCH6342-TL-H	YR	SC-88FL / MCPH6	3,000 / Tape & Reel	
MCH6342-TL-W	TK	(Pb-Free / Halogen Free)		

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6342 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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